

# METHOD AND APPARATUS OF A VARIABLE HEIGHT AND CONTROLLED FLUID FLOW PLATEN IN A CHEMICAL MECHANICAL POLISHING SYSTEM

## **ABSTRACT OF THE DISCLOSURE**

An apparatus for use in a chemical mechanical planarization (CMP) system is provided. The apparatus includes a platen capable of introducing fluid beneath a polishing pad and a platen support cover configured to surround the platen. The platen is disposed at a first level and the platen support cover is disposed at a second level, the first level being lower relative to the second level. Both the platen and the platen support cover are configured to be disposed below the polishing pad such that the polishing pad is closer to the second level than the first level. The platen support cover has a width at the second level that is substantially equal around the platen. An apparatus and method for controlling pressure beneath a polishing pad is also provided.